



## 6NM65

Preliminary

Power MOSFET

### 6.0A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

#### DESCRIPTION

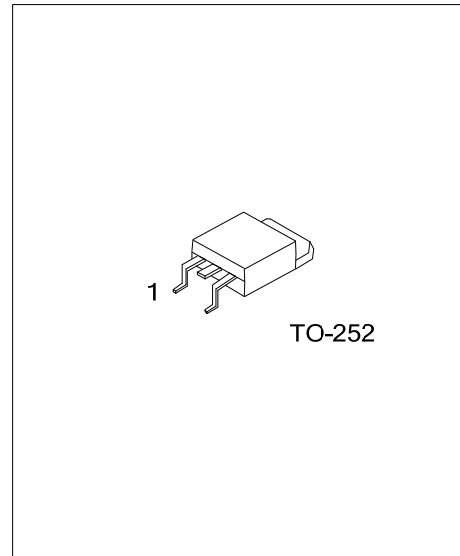
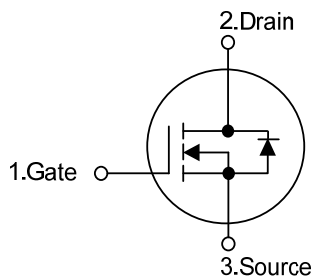
The UTC **6NM65** is an Super Junction MOSFET Structure. It uses UTC advanced planar stripe, DMOS technology to provide customers perfect switching performance, minimal on-state resistance.

The UTC **6NM65** is universally applied in electronic lamp ballasts based on half bridge topology, high efficiency switched mode power supplies, active power factor correction, etc.

#### FEATURES

- \*  $R_{DS(ON)} \leq 1.6 \Omega$  @  $V_{GS}=10V$ ,  $I_D=3.0A$
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved  $dv/dt$  capability, high ruggedness

#### SYMBOL



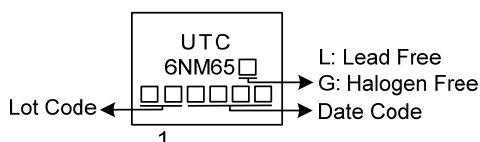
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6NM65L-TN3-R	6NM65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<b>6NM65G-TN3-R</b>		(1) Packing Type	(1) R: Tape Reel
		(2) Package Type	(2) TN3: TO-252
		(3) Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DS}$	650	V
Gate-Source Voltage		$V_{GS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	6	A
	Pulsed (Note 2)	$I_{DM}$	12	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	144	mJ
Peak Diode Recovery $dv/dt$ (Note 4)		$dv/dt$	3.2	V/ns
Power Dissipation		$P_D$	46	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3.  $L=144\text{mH}$ ,  $I_{AS}=1.4\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD}\leq 6.0\text{A}$ ,  $di/dt\leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	110	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	2.71	$^\circ\text{C}/\text{W}$

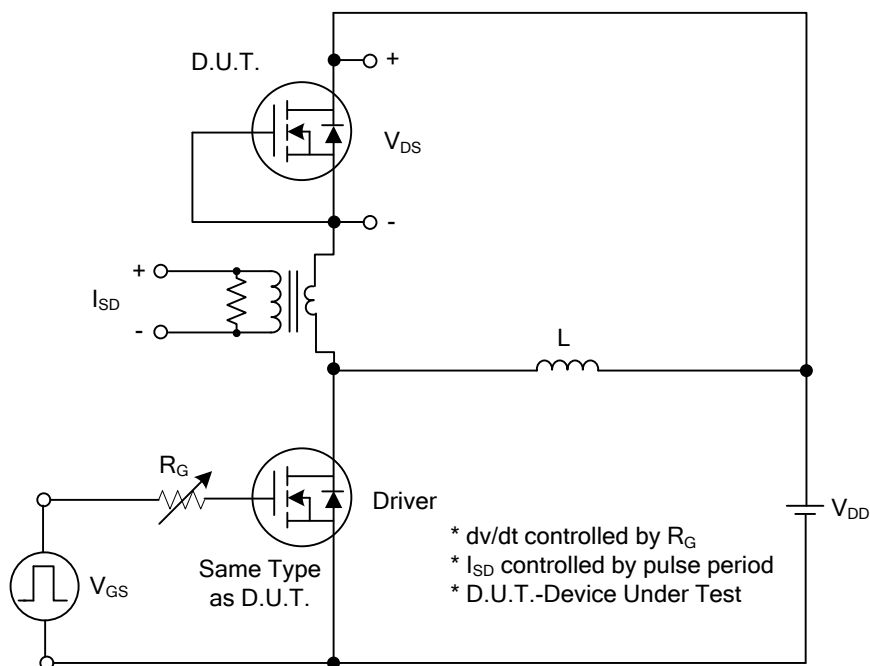
■ ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	650			V
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> = 650V, V <sub>GS</sub> = 0V			10	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V			100	nA
	Reverse		V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> =3.0A			1.6	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f =1MHz		430		pF
Output Capacitance		C <sub>OSS</sub>			78		pF
Reverse Transfer Capacitance		C <sub>RSS</sub>			16		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q <sub>G</sub>	V <sub>DS</sub> =520V, V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A (Note 1, 2)		17		nC
Gate-Source Charge		Q <sub>GS</sub>			7.5		nC
Gate-Drain Charge		Q <sub>GD</sub>			4		nC
Turn-On Delay Time		t <sub>D(ON)</sub>	V <sub>DD</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =6.0A, R <sub>G</sub> =25Ω (Note 1, 2)		9		ns
Turn-On Rise Time		t <sub>R</sub>			17		ns
Turn-Off Delay Time		t <sub>D(OFF)</sub>			30		ns
Turn-Off Fall Time		t <sub>F</sub>			29		ns
DRAIN-SOURCE DIODE CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I <sub>S</sub>				6	A
Maximum Pulsed Drain-Source Diode Forward Current		I <sub>SM</sub>				12	A
Drain-Source Diode Forward Voltage		V <sub>SD</sub>	I <sub>S</sub> =6.0A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time		t <sub>rr</sub>	I <sub>S</sub> =6.0A, V <sub>GS</sub> =0V		265		nS
Body Diode Reverse Recovery Charge		Q <sub>rr</sub>	dI/dt=100A/μs		2.75		μC

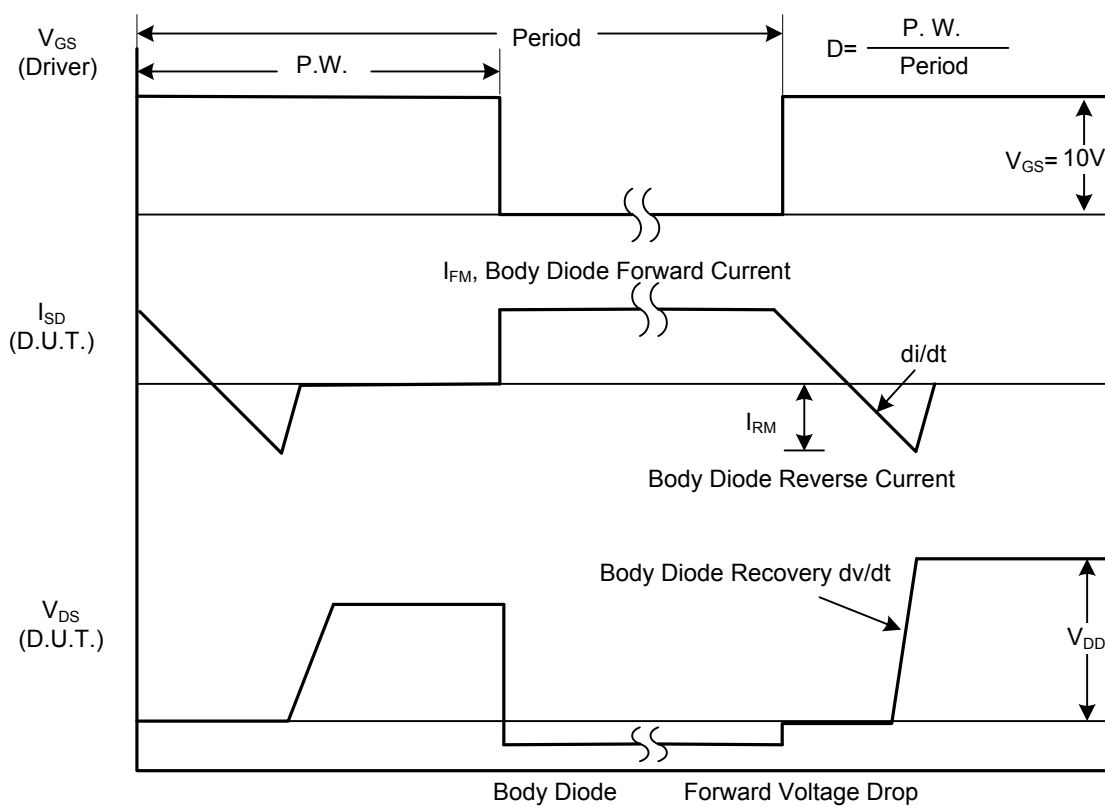
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

# ■ TEST CIRCUITS AND WAVEFORMS

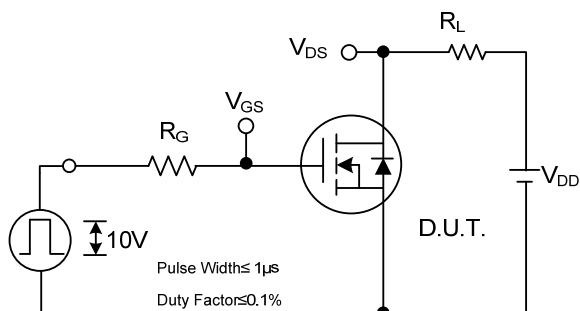


Peak Diode Recovery  $dv/dt$  Test Circuit

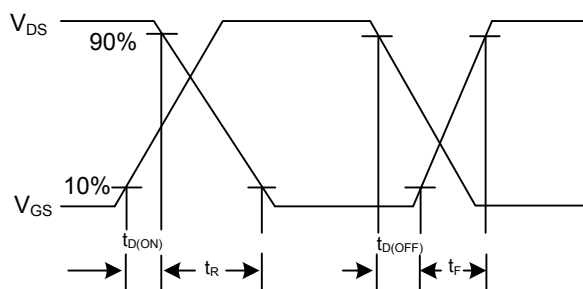


Peak Diode Recovery  $dv/dt$  Waveforms

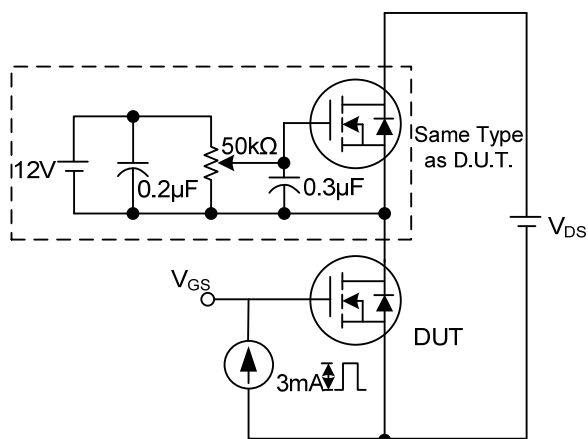
# ■ TEST CIRCUITS AND WAVEFORMS



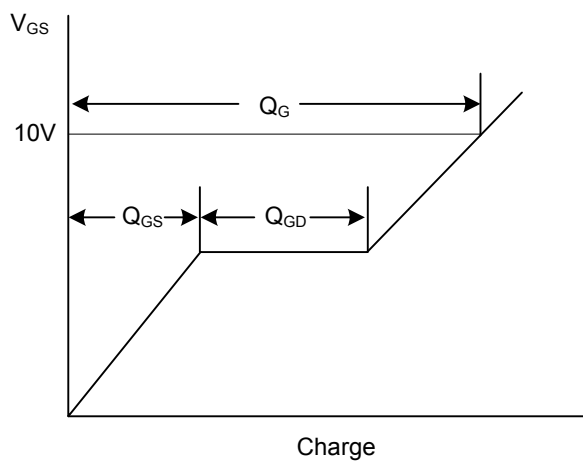
Switching Test Circuit



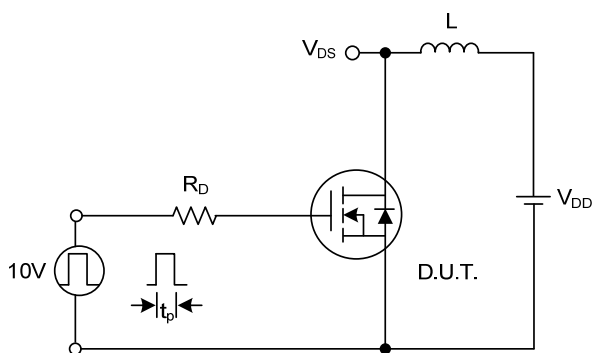
Switching Waveforms



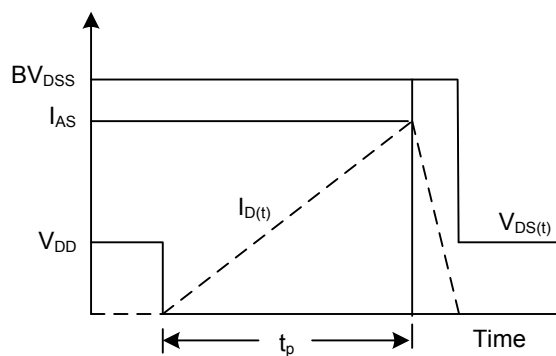
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

## ■ TYPICAL CHARACTERISTICS

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